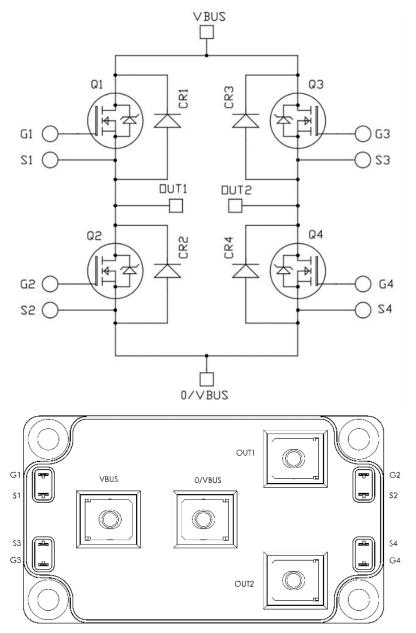
MSCSM120HM083CAG

Full Bridge SiC Power Module

Product Overview

The MSCSM120HM083CAG device is a 1200 V, 251 A full bridge silicon carbide (SiC) power module.



All ratings at T_J = 25 °C, unless otherwise specified.

Caution: These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

Features

The following are the key features of MSCSM120HM083CAG device:

- · SiC Power MOSFET
 - Low R_{DS(on)}
 - High temperature performance
- · SiC Schottky Diode
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature independent switching behavior
 - Positive temperature coefficient on VF
- · Kelvin source for easy drive
- · Low stray inductance
- M5 power connectors
- Aluminum Nitride (AIN) substrate for improved thermal performance

Benefits

The following are the benefits of MSCSM120HM083CAG device:

- · High efficiency converter
- · Outstanding performance at high frequency operation
- · Stable temperature behavior
- Direct mounting to heatsink (isolated package)
- · Low junction-to-case thermal resistance
- · RoHS Compliant

Application

The following are the applications of MSCSM120HM083CAG device:

- · Welding converters
- · Switched mode power supplies
- · Uninterruptible power supplies
- EV motor and traction drive

1. Electrical Specifications

This section provides the electrical specifications of the MSCSM120HM083CAG device.

1.1 SiC MOSFET Characteristics (per SiC MOSFET)

The following table lists the absolute maximum ratings per SiC MOSFET of the MSCSM120HM083CAG device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter		Maximum Ratings	Unit	
V _{DSS}	Drain-source voltage		1200	V	
I _D	Continuous drain current T _C = 25 °C		251	А	
		T _C = 80 °C			
I _{DM}	Pulsed drain current		500		
V _{GS}	Gate-source voltage		-10/25	V	
R _{DS(on)}	Drain-source ON resistance		10.4	mΩ	
P _D	Power dissipation	T _C = 25 °C	1042	W	

The following table lists the electrical characteristics per SiC MOSFET of the MSCSM120HM083CAG device.

Table 1-2. Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
I _{DSS}	Zero gate voltage drain current	V _{GS} = 0 V; V _{DS} = 1200 V		_	30	300	μΑ
R _{DS(on)}	Drain-Source on	V _{GS} = 20 V	T _J = 25 °C	_	8.3	10.4	mΩ
	resistance I _D = 120 A	I _D = 120 A	T _J = 175 °C	_	13.3	_	
V _{GS(th)}	Gate threshold voltage	$V_{GS} = V_{DS}$; $I_D = 3 \text{ mA}$		1.8	2.8	_	V
I _{GSS}	Gate–Source leakage current	V _{GS} = 20 V; V _{DS} = 0 V		_	_	300	nA

The following table lists the dynamic characteristics per SiC MOSFET of the MSCSM120HM083CAG device.

Table 1-3. Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
C _{iss}	Input capacitance	V _{GS} = 0 V	_	9	_	nF	
C _{oss}	Output capacitance	V _{DS} = 1000 V	_	0.81	_		
C _{rss}	Reverse transfer capacitance	f = 1 MHz	_	0.07	_		
Q_g	Total gate charge	V _{GS} = -5 V/20 V		_	696	_	nC
Q _{gs}	Gate-source charge	V _{Bus} = 800 V		_	123	_	
Q_{gd}	Gate-drain charge	I _D = 120 A	_	150	_		
T _{d(on)}	Turn-on delay time	T _J = 150 °C	_	56	_	ns	
T _r	Rise time	$V_{GS} = -5 \text{ V}/20 \text{ V}$		_	55	_	
T _{d(off)}	Turn-off delay time	V _{Bus} = 600 V		_	166	_	
T _f	Fall time	I_D = 150 A R_{GON} = 2.7 Ω R_{GOFF} = 1.6 Ω			67	_	
E _{on}	Turn-on energy	Inductive switching	T _J = 150 °C	_	3	_	mJ
E _{off}	Turn-off energy	V_{GS} = -5 V/20 V V_{Bus} = 600 V I_{D} = 150 A R_{GON} = 2.7 Ω R_{GOFF} = 1.6 Ω	T _J = 150 °C	_	2.7	_	
R _{Gint}	Internal gate resistance			_	2	_	Ω
R _{thJC}	Junction-to-case therm	nal resistance		_	_	0.144	°C/W

The following table lists the body diode ratings and characteristics per SiC MOSFET of the MSCSM120HM083CAG device.

Table 1-4. Body Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
V_{SD}	Diode forward voltage	V _{GS} = 0 V; I _{SD} = 120 A		4	_	V
		$V_{GS} = -5 \text{ V}; I_{SD} = 120 \text{ A}$	_	4.2	_	
t _{rr}	Reverse recovery time	I _{SD} = 120 A	_	90	_	ns
Q _{rr}	Reverse recovery charge	$V_{GS} = -5 V$	_	1650	_	nC
I _{rr}	Reverse recovery current	V _R = 800 V		41	_	Α
		di _F /dt = 3000 A/μs				

1.2 SiC Schottky Diode Characteristics (per SiC Diode)

The following table lists the SiC Schottky diode ratings and characteristics of the MSCSM120HM083CAG device.

Table 1-5. SiC Diode Ratings and Characteristics (Per SiC Diode)

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V _{RRM}	Peak repetitive reverse volt	age		_	_	1200	V
I _{RRM}	Reverse leakage current	V _R = 1200 V	T _J = 25 °C	_	30	600	μA
				_	450	_	
I _F	DC forward current	— T _C = 100 °C		_	90	_	Α
V _F	Diode forward voltage I _F = 90 A		T _J = 25 °C	_	1.5	1.8	V
			T _J = 175 °C	_	2.1	_	
Q_C	Total capacitive charge	V _R = 600 V		_	390	_	nC
С	Total capacitance	f = 1 MHz, V _R = 400 V		_	423	_	pF
	f = 1 MHz, V _R		00 V	_	315	_	
R _{thJC}	Junction-to-case thermal re	sistance		_	_	0.34	°C/W

1.3 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the MSCSM120HM083CAG device.

Table 1-6. Thermal and Package Characteristics

Symbol	Characteristic	Characteristic				
V _{ISOL}	RMS isolation voltage, any terminal to ca	4000	_	V		
T _J	Operating junction temperature range	Operating junction temperature range				°C
T _{JOP}	Recommended junction temperature und	Recommended junction temperature under switching conditions				
T _{STG}	Storage case temperature	Storage case temperature				
T _C	Operating case temperature	Operating case temperature				
Torque	Mounting torque	To heatsink	M6	3	5	N.m
		For terminals	M5	2	3.5	
Wt	Package weight	Package weight			300	g

1.4 Typical SiC MOSFET Performance Curve

This section shows the typical SiC MOSFET performance curves of the MSCSM120HM083CAG device.

Figure 1-1. Maximum Thermal Impedance

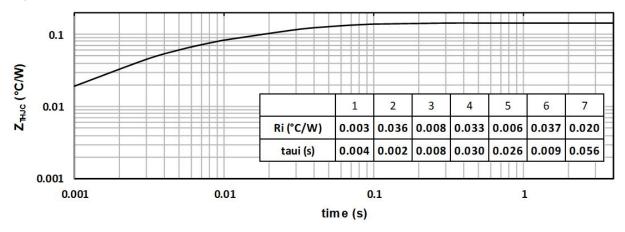


Figure 1-2. Output Characteristics, $T_J = 25$ °C

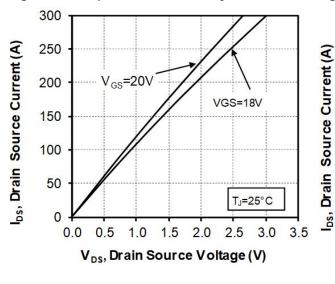


Figure 1-3. Output Characteristics, $T_J = 175$ °C

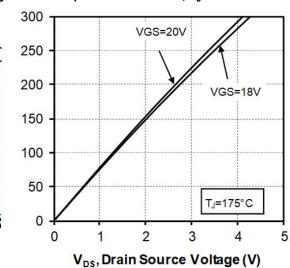


Figure 1-4. Normalized R_{DS(on)} vs. Temperature

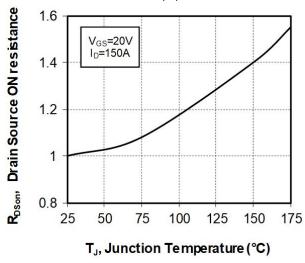


Figure 1-5. Transfer Characteristics

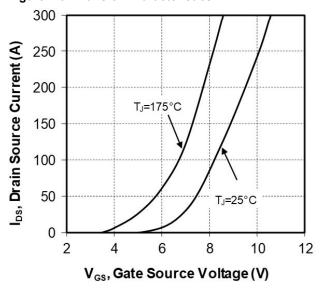


Figure 1-6. Switching Energy vs. Rg

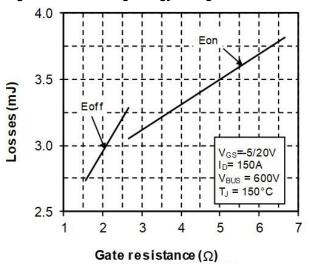


Figure 1-7. Switching Energy vs. Current

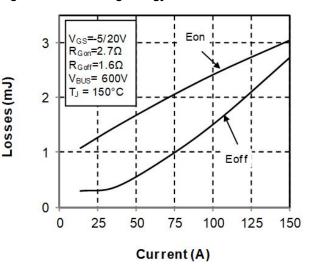


Figure 1-8. Capacitance vs. Drain Source Voltage

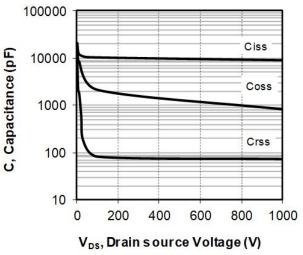


Figure 1-9. Gate Charge vs. Gate Source Voltage

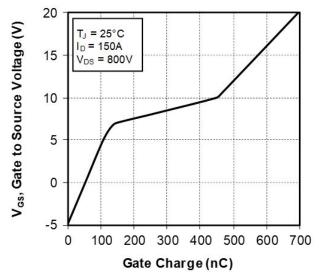


Figure 1-10. Body Diode Characteristics, T_J = 25 °C

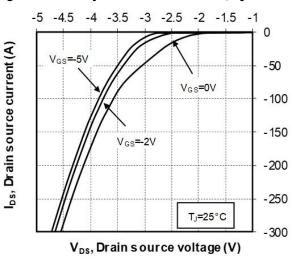


Figure 1-11. 3rd Quadrant Characteristics, T_J = 25 °C

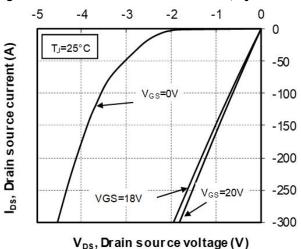
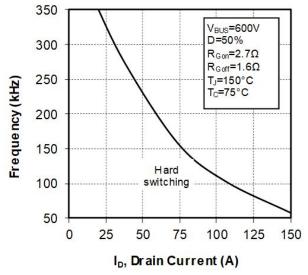


Figure 1-12. Body Diode Characteristics, T_J = 175 °C Figure 1-13. 3rd Quadrant Characteristics, T_J = 175 °C -3 -2.5 -2 -1.5 -1 0 0 los, Drain source current (A) V_{GS}=-5V l_{DS}, Drain source current (A) T_J=175°C -50 -50 V_{GS}=-2V -100 -100 V_{GS}=0V -150 VGS=18V -150 -200 -200 -250 -250T_J=175°C V_{GS}=20V -300 -300 V_{DS}, Drain source voltage (V) V_{DS}, Drain source voltage (V)

Figure 1-14. Operating Frequency vs Drain Current



1.5 Typical SiC Diode Performance Curves

This section shows the typical SiC diode performance curves of the MSCSM120HM083CAG device.

Figure 1-15. Maximum Thermal Impedance

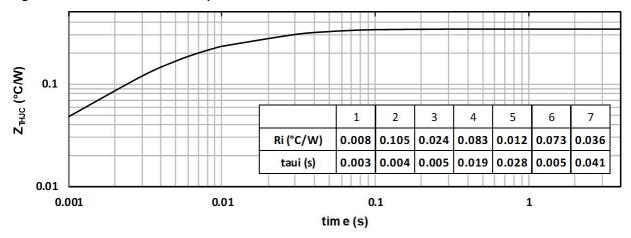


Figure 1-16. Forward Characteristics

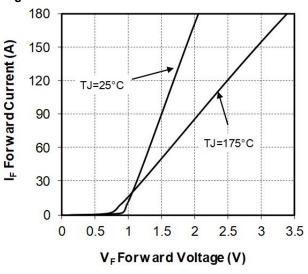
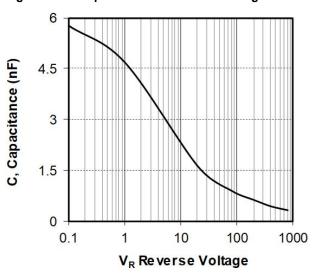


Figure 1-17. Capacitance vs. Reverse Voltage



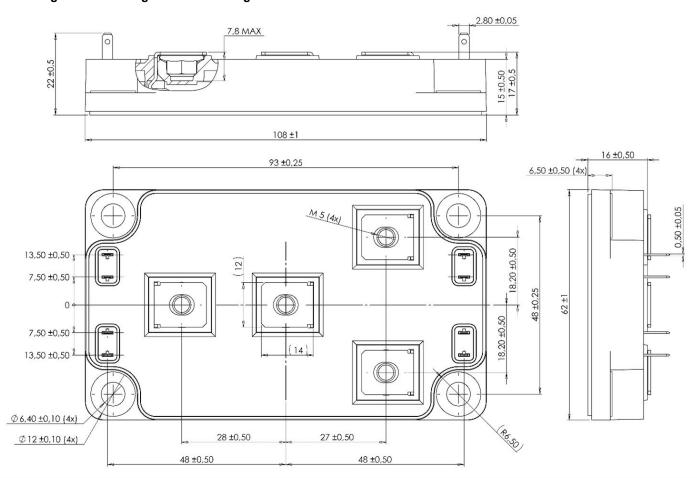
2. Package Specifications

The following section shows the package specification of the MSCSM120HM083CAG device.

2.1 Package Outline Drawing

The following figure shows the package outline drawing of the MSCSM120HM083CAG device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



Note: See application note APT0601—Mounting Instructions for SP6 Power Modules.

3. Revision History

Revision	Date	Description
Α	04/2021	This is the first publication of this document.

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